Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
LED	Forward current	I_F	50	mA
	Forward current derating (Ta ≥ 39°C)	ΔI_F/°C	-0.7	mA/°C
	Peak forward current (100 μs pulse, 100 pps)	I_{FP}	1	A
	Reverse Voltage	V_R	5	V
	Diode power dissipation	P_D	50	mW
	Diode power dissipation derating (Ta >39 °C)	ΔP_D/°C	-0.58	mW/°C
	Junction temperature	T_j	125	°C
Detector	Collector-emitter voltage	V_{CEO}	55	V
	Collector-base voltage (TLP331)	V_{CBO}	80	V
	Emitter-collector voltage	V_{ECO}	7	V
	Emitter-base voltage (TLP331)	V_{EBO}	7	V
	Collector current	I_C	50	mA
	Power dissipation	P_C	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP_C/°C	-1.5	mW/°C
	Junction temperature	T_j	125	°C
Storage temperature range		T_{stg}	-55 to 125	°C
Operating temperature range		T_{opr}	-55 to 100	°C
Lead soldering temperature (10 s)		T_{sol}	260	°C
Total package power dissipation		P_T	250	mW
Total package power dissipation derating (Ta ≥ 25°C)		P_T/°C	-2.5	mW/°C
Isolation voltage (AC, 60 s, RH ≤ 60 %)	(Note 1)	BV_S	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4, 5 and 6 shorted together.

Recommended Operating Conditions

Characteristics	Symbol	Min	Typ.	Max	Unit
Supply voltage	V_{CC}	—	5	25	V
Forward current	I_F	—	1.6	25	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	-25	—	75	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Electrical Characteristics (Ta = 25°C)

	Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
LED	Forward voltage	V_F	I_F = 10 mA	1.0	1.15	1.3	V
	Reverse current	I_R	V_R = 5 V	—	—	10	μA
	Capacitance	C_T	V = 0 V, f = 1 MHz	—	30	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 0.5 mA	55	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$	I_E = 0.1 mA	7	—	—	V
	Collector-base breakdown voltage (TLP331)	$V_{(BR)CBO}$	I_C = 0.1 mA	80	—	—	V
	Emitter-base breakdown voltage (TLP331)	$V_{(BR)EBO}$	I_E = 0.1 mA	7	—	—	V
	Collector dark current	I_{CEO}	V_{CE} = 24 V	—	10	100	nA
			V_{CE} = 24 V, Ta = 85 °C	—	2	50	μA
	Collector dark current (TLP331)	I_{CER}	V_{CE} = 24 V, Ta = 85 °C R_{BE} = 1 MΩ	—	0.5	10	μA
	Collector dark current (TLP331)	I_{CBO}	V_{CB} = 10 V	—	0.1	—	nA
	DC forward current gain (TLP331)	h_{FE}	V_{CE} = 5 V, I_C = 0.5 mA	—	1000	—	—
	Capacitance (collector to emitter)	C_{CE}	V = 0 V , f = 1 MHz	—	12	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	I_C/I_F	I_F = 1 mA, V_{CE} = 0.5 V	100	—	1200	%
		Rank BV	200	—	1200	
Low input CTR	$I_C/I_{F(low)}$	I_F = 0.5 mA, V_{CE} = 1.5 V	50	—	—	%
		Rank BV	100	—	—	
Base photo-current (TLP331)	I_{PB}	I_F = 1 mA, V_{CB} = 5 V	—	10	—	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 0.5 mA, I_F = 1 mA	—	—	0.4	V
		I_C = 1 mA, I_F = 1 mA	—	0.2	—	
		Rank BV	—	—	0.4	

Coupled Electrical Characteristics (Ta = 25 to 75°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	I_C/I_F	I_F = 1 mA, V_{CE} = 0.5 V	50	—	—	%
		Rank BV	100	—	—	
Low input CTR	$I_C/I_{F(low)}$	I_F = 0.5 mA, V_{CE} = 1.5 V	—	50	—	%
		Rank BV	—	100	—	

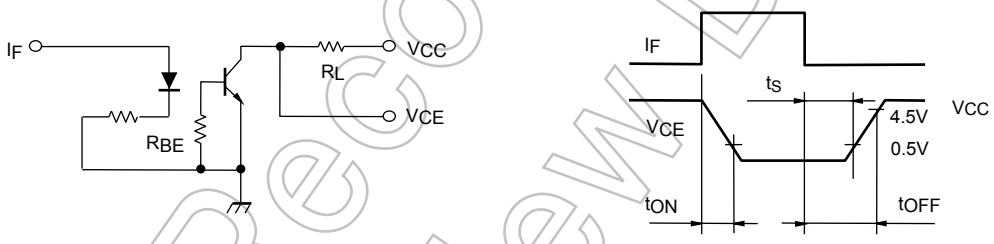
Isolation Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Capacitance (input to output)	C_S	V_S = 0 V, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	V = 500 V, RH ≤ 60 %	5×10^{10}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 60 s	5000	—	—	Vrms

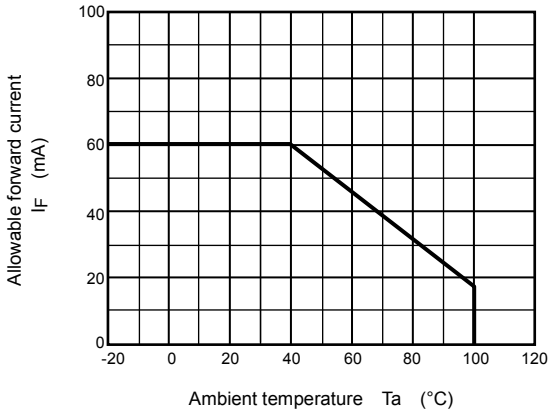
Switching Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Rise time	t_r	V_{CC} = 10 V, I_C = 2 mA R_L = 100 Ω	—	8	—	μs
Fall time	t_f		—	8	—	
Turn-on time	t_{on}		—	10	—	
Turn-off time	t_{off}		—	8	—	
Turn-on time	t_{ON}	R_L = 4.7 kΩ (Fig.1) R_{BE} = OPEN V_{CC} = 5 V, I_F = 1.6 mA	—	10	—	μs
Storage time	t_S		—	50	—	
Turn-off time	t_{OFF}		—	300	—	
Turn-on time	t_{ON}	R_L = 4.7 kΩ (Fig.1) R_{BE} = 470 kΩ (TLP331) V_{CC} = 5 V, I_F = 1.6 mA	—	12	—	μs
Storage time	t_S		—	30	—	
Turn-off time	t_{OFF}		—	100	—	

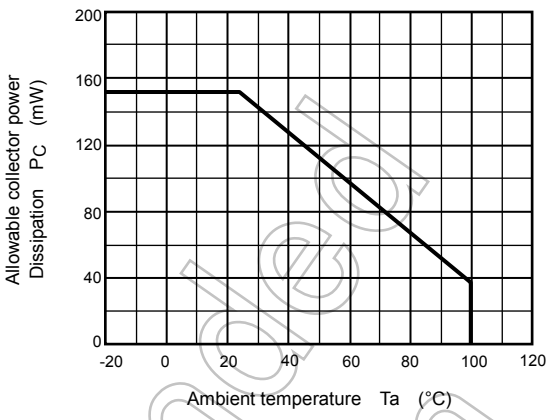
Fig. 1 Switching time test circuit



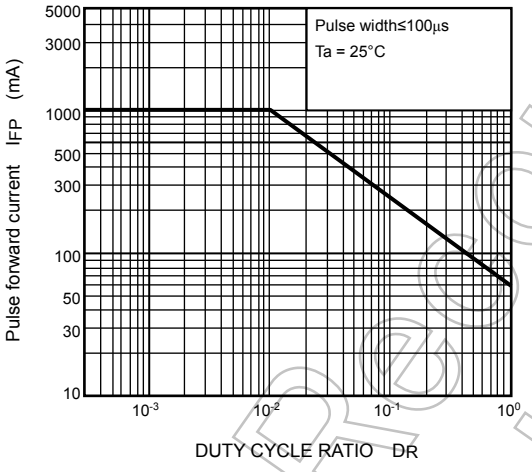
I_F – Ta



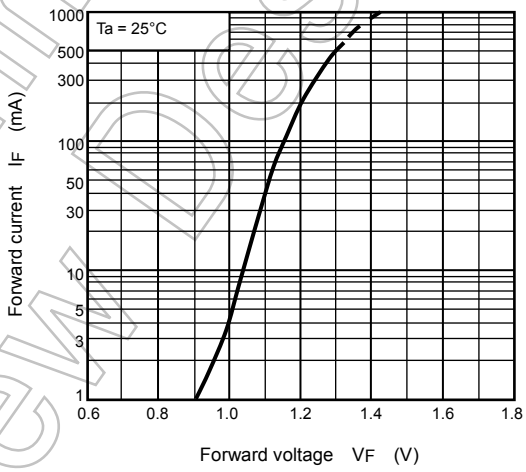
P_C – Ta



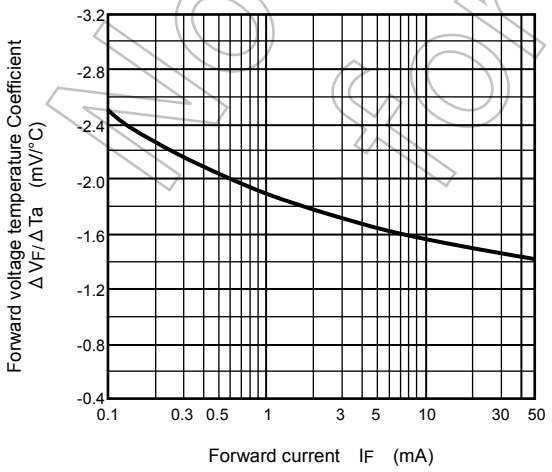
I_{FP} – D_R



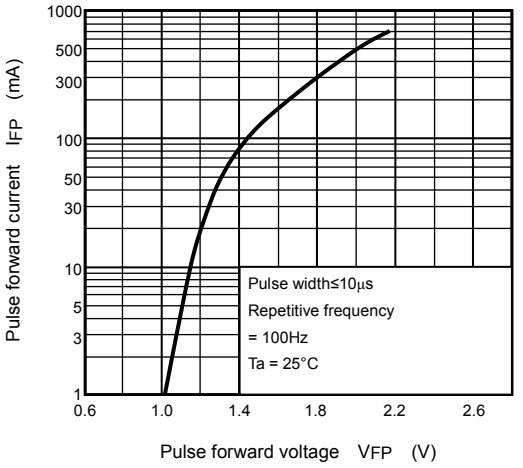
I_F – V_F



$\Delta V_F / \Delta Ta$ – I_F



I_{FP} – V_{FP}



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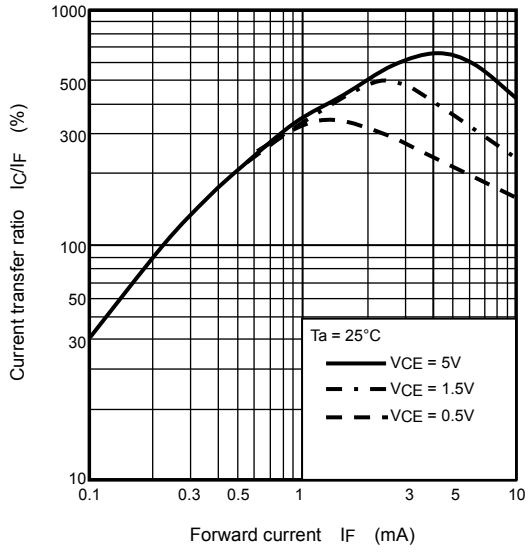
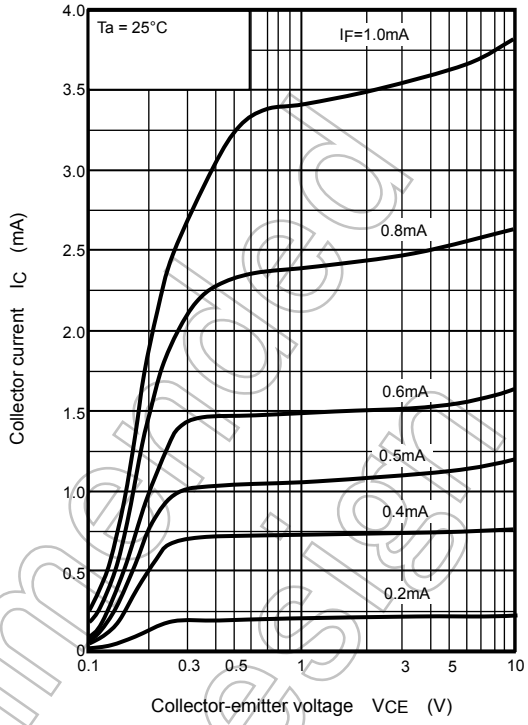
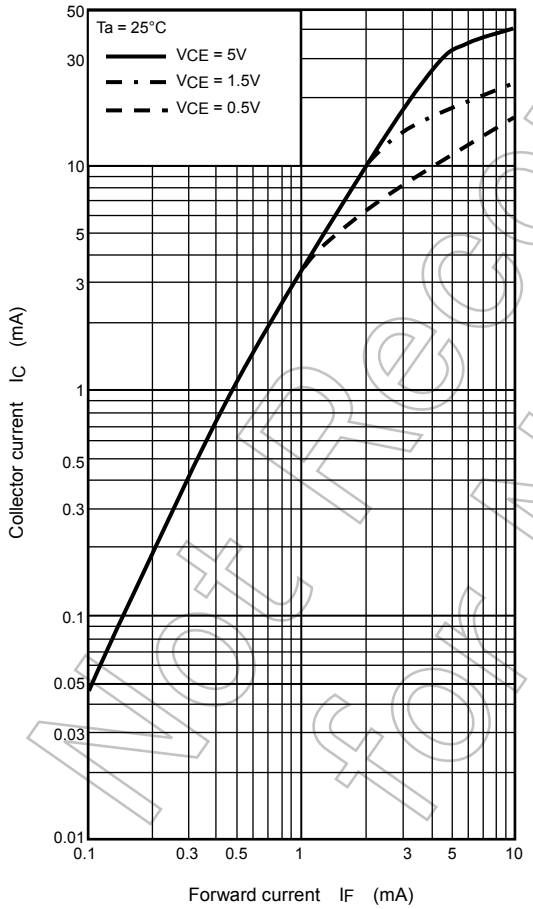
$I_C/I_F - I_F$



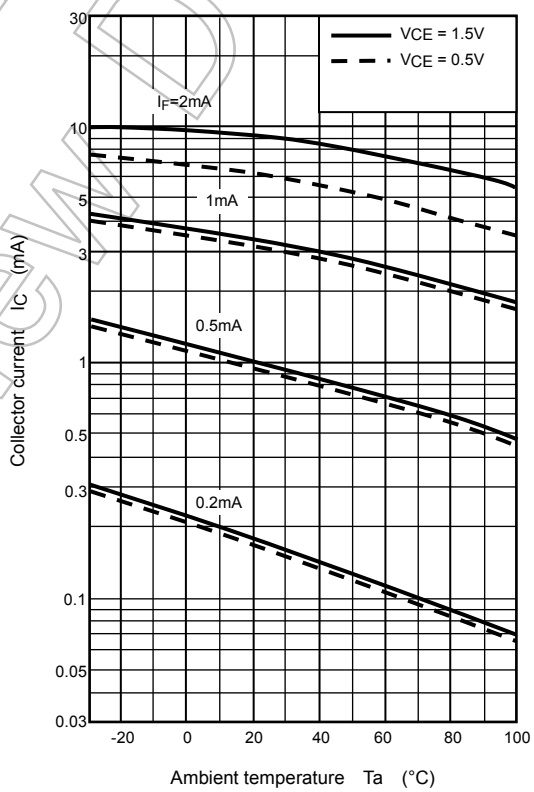
$I_C - V_{CE}$



$I_C - I_F$



$I_C - Ta$



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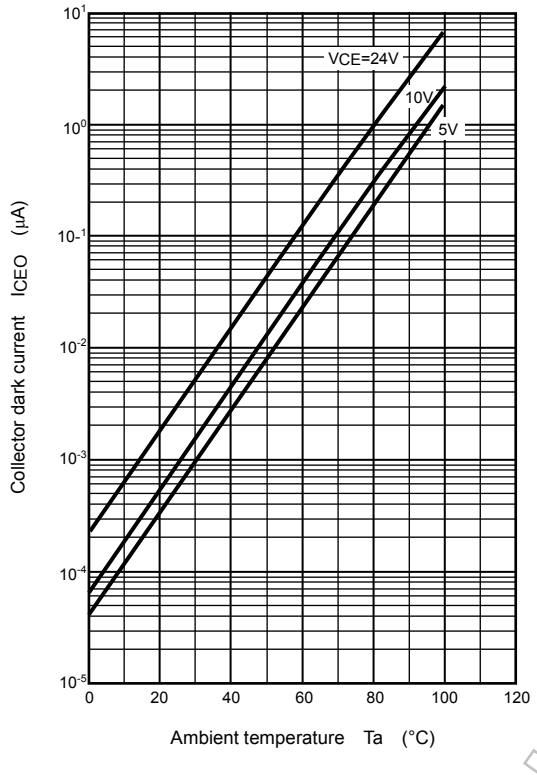
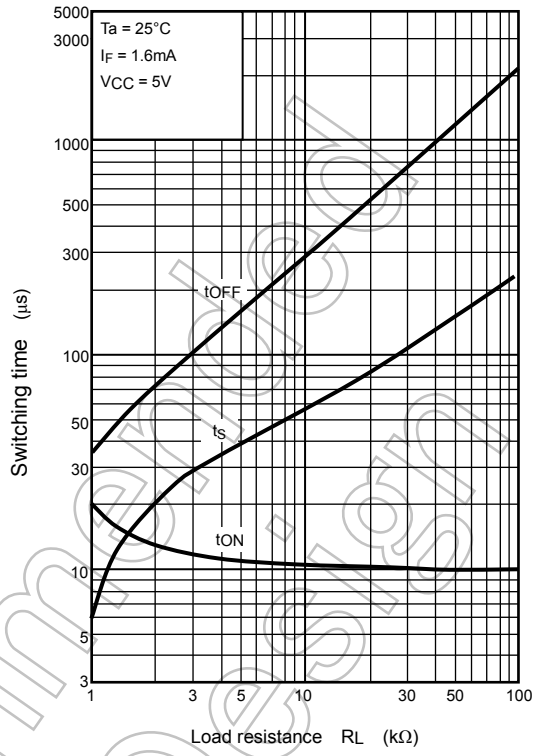
I_{CEO} – Ta



Switching Time – R_L



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